GL195

PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

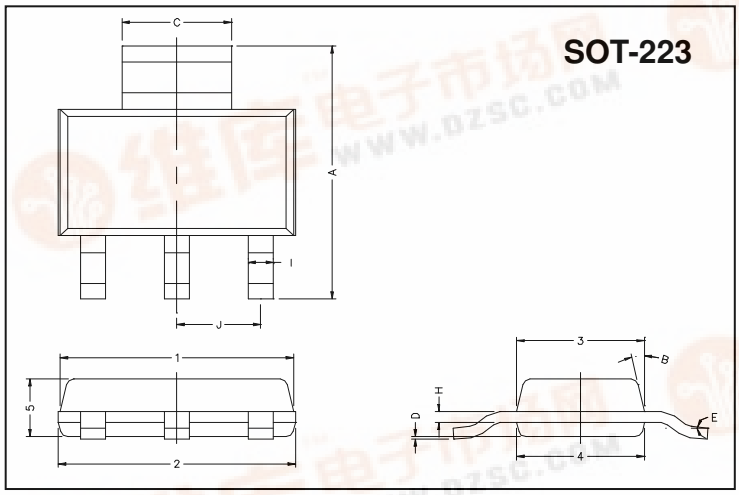
Description

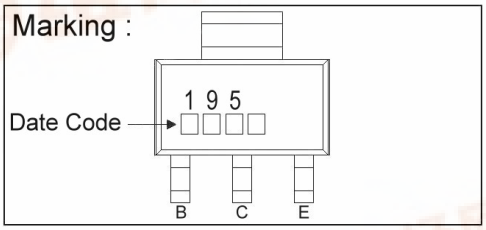
The GL195 is designed for medium power amplifier applications.

Features

- -60 Volt V_{CEO}
- 1 Amp continuous current
- Complementary to GL194

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13°TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25℃

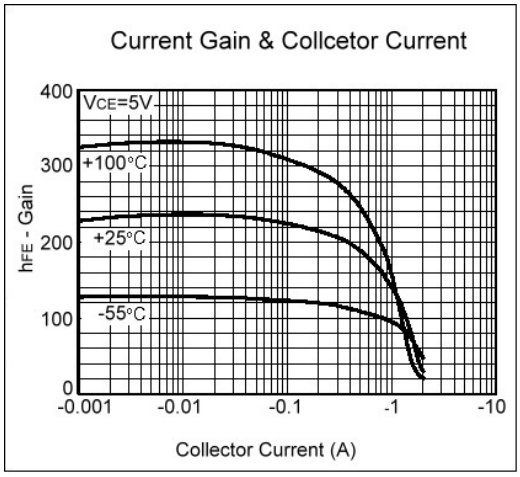
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55~+150	℃
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current (DC)	I_C	-1	A
Collector Current (Pulse)	I_C	-2	A
Base Current	I_B	-200	mA
Total Power Dissipation	P_D	2	W

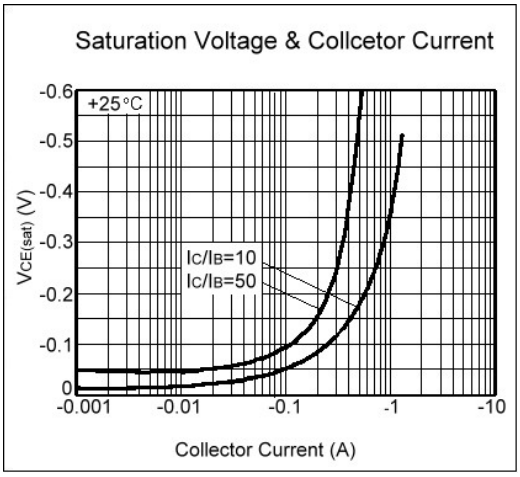
Electrical Characteristics (Ta = 25℃, unless otherwise stated)

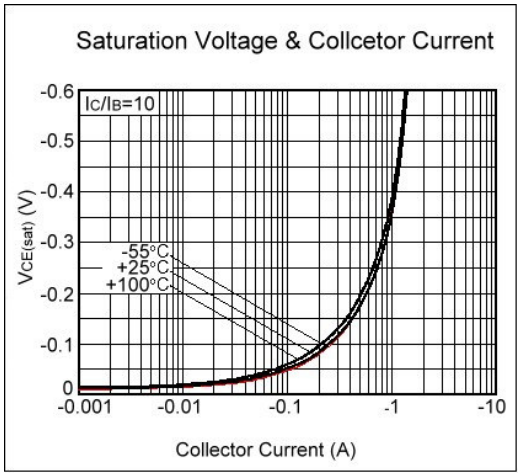
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-80	-	-	V	I_C=-100uA , I_E=0
*BV_{CEO}	-60	-	-	V	I_C=-10mA, I_B=0
BV_{EBO}	-5	-	-	V	I_E=-100uA ,I_C=0
I_{CBO}	-	-	-100	nA	V_{CB}=-60V, I_E=0
I_{CES}	-	-	-100	nA	V_{CES}=-60V
I_{EBO}	-	-	-100	nA	V_{EB}=-4V, I_C=0
*$V_{CE(sat)}$1	-	-	-0.3	V	I_C=-500mA, I_B=-50mA
*$V_{CE(sat)}$2	-	-	-0.6	V	I_C=-1A, I_B=-100mA
*$V_{BE(sat)}$	-	-	-1.2	V	I_C=-1A, I_B=-100mA
*$V_{BE(on)}$	-	-	-1.0	V	V_{CE}=-5V, I_C=-1A
*h_{FE}1	100	-			V_{CE}=-5V, I_C=-1mA
*h_{FE}2	100	-	300		V_{CE}=-5V, I_C=-500mA
*h_{FE}3	80	-			V_{CE}=-5V, I_C=-1A
*h_{FE}4	15	-			V_{CE}=-5V, I_C=-2A
fT	150	-	-	MHz	V_{CE}=-10V, I_C=-50mA, f=100MHz
Cob	-	-	10	pF	V_{CB}=-10V, I_E=0, f=1MHz

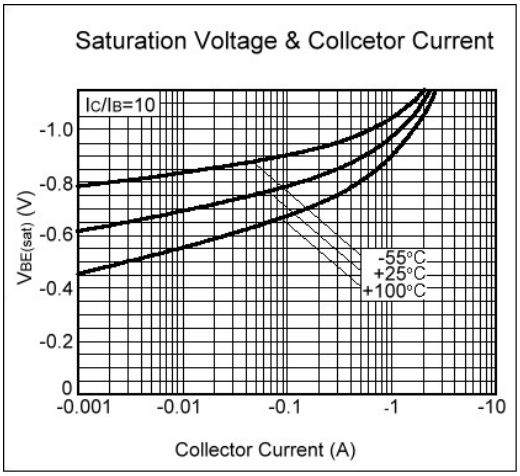
***Measured under pulse condition. Pulse width=300μs, Duty Cycle≦2%**

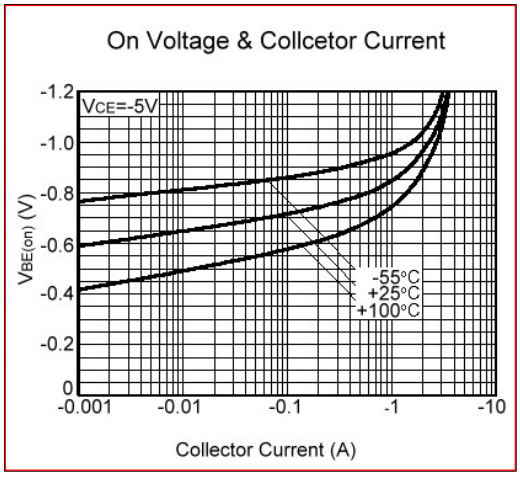
Characteristics Curve

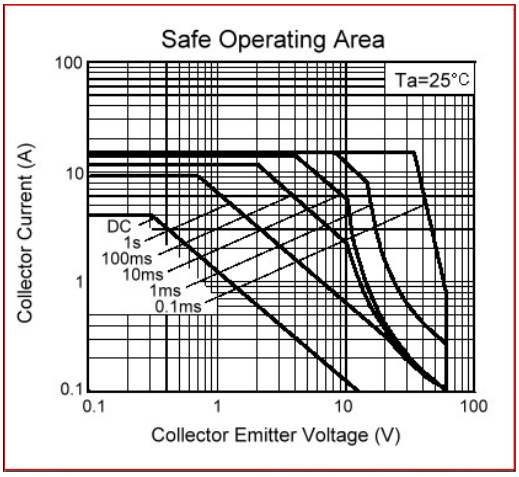












Head Office And Factory:
- **Taiwan**: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
  TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China**: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
  TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165